

# Thierry Ouisse

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8030635/publications.pdf>

Version: 2024-02-01

46  
papers

683  
citations

840119

11  
h-index

580395

25  
g-index

47  
all docs

47  
docs citations

47  
times ranked

922  
citing authors

#	ARTICLE	IF	CITATIONS
1	Electronic and vibrational properties of $V_2C$ -based MXenes: From experiments to first-principles modeling. <i>Physical Review B</i> , 2018, 97, .	1.1	162
2	Influence of series resistances and interface coupling on the transconductance of fully-depleted silicon-on-insulator MOSFETs. <i>Solid-State Electronics</i> , 1992, 35, 141-149.	0.8	69
3	Variable range hopping and thermally activated transport in molybdenum-based MXenes. <i>Physical Review B</i> , 2018, 98, .	1.1	66
4	Identification of Dislocations in Synthetic Chemically Vapor Deposited Diamond Single Crystals. <i>Crystal Growth and Design</i> , 2016, 16, 2741-2746.	1.4	52
5	Raman scattering from $Ti_3SiC_2$ single crystals. <i>Applied Physics Letters</i> , 2011, 98, 081912.	1.5	49
6	Magnetotransport in the MAX phases and their 2D derivatives: MXenes. <i>Materials Research Letters</i> , 2017, 5, 365-378.	4.1	47
7	Synthesis and Characterization of Double Solid Solution $(Zr,Ti)_2(Al,Sn)C$ MAX Phase Ceramics. <i>Inorganic Chemistry</i> , 2019, 58, 6669-6683.	1.9	45
8	Mechanical Exfoliation of Select MAX Phases and $Mo_4Ce_4Al_7C_3$ Single Crystals to Produce MAXenes. <i>Small</i> , 2020, 16, e1905784.	5.2	30
9	Modeling of the Growth Rate during Top Seeded Solution Growth of SiC Using Pure Silicon as a Solvent. <i>Crystal Growth and Design</i> , 2012, 12, 909-913.	1.4	25
10	Electronic structure of $C_rV_2AlC$ as observed by angle-resolved photoemission spectroscopy. <i>Physical Review B</i> , 2017, 96, .	1.1	19
11	Elementary processes governing $V_2AlC$ chemical etching in HF. <i>RSC Advances</i> , 2020, 10, 25266-25274.	1.7	19
12	Electrical Characterization of the AlN/Si(111) System. <i>Materials Science Forum</i> , 1998, 264-268, 1389-1392.	0.3	9
13	Unified description of the electronic structure of M <sub>2</sub> AC nanolamellar carbides. <i>Physical Review B</i> , 2019, 100, .	1.1	8
14	Electronic structure of $V_2AlC$ . <i>Physical Review B</i> , 2018, 98, .	1.1	7
15	Unintentional incorporation of contaminants during chemical vapour deposition of silicon carbide. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1995, 29, 134-137.	1.7	6
16	Photon Emission Analysis of Defect-Free 4H-SiC pn Diodes in Avalanche Regime. <i>Materials Science Forum</i> , 2002, 389-393, 1293-1296.	0.3	6
17	Structural, Electronic and Vibrational Properties of $Al_4C_3$ . <i>Physica Status Solidi (B): Basic Research</i> , 2019, 256, 1900037.	0.7	5
18	Conduction and Trapping in RF MEMS capacitive switches with a SiN layer. , 2009, , .		4

#	ARTICLE	IF	CITATIONS
19	Large Area Quasi-Free Standing Monolayer Graphene on 3C-SiC(111). Materials Science Forum, 2012, 717-720, 617-620.	0.3	4
20	Open Issues in SiC Bulk Growth. Materials Science Forum, 2014, 778-780, 3-8.	0.3	4
21	Near Fermi level electronic structure of Ti <sub>3</sub> SiC <sub>2</sub> revealed by angle-resolved photoemission spectroscopy. Physical Review B, 2020, 102, .	1.1	4
22	Elastic properties and hardness values of $\sqrt{V} \text{AlC}$ and $\sqrt{C} \text{r}^2 \text{AlC}$	0.9	4
23	Stationary Occupied State in a Coulomb Potential with Electron Screening. Journal of the Physical Society of Japan, 1998, 67, 4157-4163.	0.7	3
24	Improvements of the Continuous Feed-Physical Vapor Transport Technique (CF-PVT) for the Seeded Growth of 3C-SiC Crystals. Materials Science Forum, 2010, 645-648, 63-66.	0.3	3
25	Study of the Spontaneous Nucleation of 3C-SiC Single Crystals Using CF-PVT Technique. Materials Science Forum, 0, 645-648, 55-58.	0.3	3
26	Heavily p-Type Doping of Bulk 6H-SiC and 3C-SiC Grown from Al-Si Melts. Materials Science Forum, 2010, 645-648, 59-62.	0.3	3
27	Effect of Aluminum during the High Temperature Solution Growth of Si-Face 4H-SiC. Materials Science Forum, 0, 858, 37-40.	0.3	3
28	Mo <sub>4</sub> Ce <sub>4</sub> Al <sub>7</sub> C <sub>3</sub> : A nanolamellar ferromagnetic Kondo lattice. Physical Review B, 2020, 102, .	1.1	3
29	Neutral impurity scattering with electron screening. Physica B: Condensed Matter, 1999, 270, 262-271.	1.3	2
30	Growth Rate Prediction in SiC Solution Growth Using Silicon as Solvent. Materials Science Forum, 2012, 717-720, 69-72.	0.3	2
31	Observation of nonstationary transport in deep submicron channel metal oxide semiconductor transistors with Shubnikov-de Haas oscillations. Journal of Applied Physics, 1994, 75, 4226-4232.	1.1	1
32	Impact Ionization in 6H-SiC MOSFETs. Materials Science Forum, 1998, 264-268, 1009-1012.	0.3	1
33	Comparison of Thermodynamic Databases for the Modeling of SiC Growth by PVT. Materials Science Forum, 0, 778-780, 35-38.	0.3	1
34	Spiral Step Dissociation on PVT Grown SiC Crystals. Materials Science Forum, 0, 778-780, 39-42.	0.3	1
35	Interaction between Vapor Species and Graphite Crucible during the Growth of SiC by PVT. Materials Science Forum, 2014, 778-780, 31-34.	0.3	1
36	Fermi surface and band structure of Ti <sub>2</sub> SnC as observed by angle-resolved photoemission spectroscopy. Physical Review B, 2021, 104, .	1.1	1

#	ARTICLE	IF	CITATIONS
37	Ion Implantation Enhanced Exfoliation Efficiency of V <sub>2</sub> AlC Single Crystals: Implications for Large V <sub>2</sub> CT <sub>z</sub> Nanosheet Production. ACS Applied Nano Materials, 2022, 5, 8029-8037.	2.4	1
38	Properties of Transmission Lines on Various SiC Substrates. Materials Science Forum, 2000, 338-342, 1267-1270.	0.3	0
39	Noise Behavior of 4H-SiC MESFETs at Low Drain Voltage. Materials Science Forum, 2001, 353-356, 703-706.	0.3	0
40	Hot-Carrier Luminescence in 4H-SiC MESFETs. Materials Science Forum, 2002, 389-393, 1371-1374.	0.3	0
41	Dislocation-Induced Birefringence in Silicon Carbide. Materials Science Forum, 2009, 615-617, 271-274.	0.3	0
42	Optical Investigation of Defect Filtering Effects in Bulk 3C-SiC Crystals Grown by the CF-PVT Method Using a Necking Technique. Materials Science Forum, 2011, 679-680, 169-172.	0.3	0
43	Identification of the Basal Plane Component of the Burgers Vector of Small Dislocations in 6H SiC Using Birefringence Microscopy. Materials Science Forum, 0, 717-720, 331-334.	0.3	0
44	Absence of Back Stress Effect in the PVT Growth of 6H Silicon Carbide. Materials Science Forum, 0, 740-742, 48-51.	0.3	0
45	Stationary Occupied State in a Coulomb Potential with Electron Screening. Journal of the Physical Society of Japan, 1999, 68, 2150-2150.	0.7	0
46	Magnetic properties of the $T_j$ ETQq0 0 0 rgBT /Overlock 10 Tf		